

The proposed method for the integrated estimation of structural efficiency of monocrystals, which are used to produce semiconductor and optoelectronic devices, consists in determining the characteristic that defines the changes of the Bragg refraction angle, the maximal value of the characteristic ( $R_m$ ), the width of the characteristic at the level of  $0.2R_m$  from the axis, and the ratio between the said parameters that is used to estimate the structural efficiency of the monocrystal. The present invention provides a possibility to increase the analysis accuracy and use samples of different width.